Flat Gain, High IP3

Monolithic Amplifier

CMA-63+

0.01 to 6 GHz

The Big Deal

- Ceramic, Hermetically Sealed, Nitrogen filled
- Low profile case, .045" high
- High Gain
- Broadband High Dynamic Range without external Matching Components



CASE STYLE: DL1721

MIL Screening Available Please consult Applications Dept.

Product Overview

CMA-63+ (RoHS compliant) is a wideband amplifier fabricated using HBT technology and offers high gain over a broad frequency range and with high IP3. In addition, the CMA-63+, has good input and output return loss over a broad frequency range without the need for external matching components and has demonstrated excellent reliability. The MMIC amplifier is bonded to a multilayer integrated LTCC substrate, and then hermetically sealed under a controlled nitrogen atmosphere with gold-plated covers and eutectic AuSn solder. These amplifiers are capable of meeting MIL requirements for gross leak, fine leak, thermal shock, vibration, acceleration, mechanical shock, and HTOL. The testing can be done if requested.

Kev Features

Feature	Advantages		
Broad Band: 0.01 to 6.0 GHz	Broadband covering primary wireless communications bands: Cellular, PCS, LTE, WiMAX, SATELLITE IF		
Flat Gain	±1.5 dB over 50 to 3000 MHz; eliminates need for gain flattening for most application		
High IP3 vs. DC power Consumption 35 dBm typical at 0.05 GHz 35 dBm typical at 0.8 GHz	The CMA-63+ matches industry leading IP3 performance relative to device size and power consumption. The combination of the design and HBT Structure provides enhanced linearity over a broad frequency range as evidence in the IP3 being typically 16 dB above the P 1dB point to 0.8 GHz. This feature makes this amplifier ideal for use in: • Driver amplifiers for complex waveform up converter paths • Drivers in linearized transmit systems		
No External Matching Components Required	CMA-63+ provides Input and Output Return Loss of 15 dB up to 3 GHz without the need any external matching components		
Ceramic Hermetic Package	Low Inductance, repeatable performance, excellent reliability.		

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B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.

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Flat Gain, High IP3

Monolithic Amplifier

0.01-6 GHz

Product Features

- Flat Gain, ±1.0 dB over 50-3000 MHz
- Gain, 20 dB typ. at 2 GHz
- High Pout, P1dB 18.4 dBm typ. at 2 GHz
- High IP3, 34.6 dBm typ. at 50 MHz; 32.0 dBm at 2GHz
- Excellent ESD protection, Class 1C for HBM
- Small size 3mm x 3mm x 1.14mm
- · Ceramic, hermetic, Nitrogen filled
- No external matching components required
- May be used as a replacement for SPF5043Z a,b

Typical Applications

- · Base station infrastructure
- Portable Wireless
- CATV & DBS
- MMDS & Wireless LAN
- LTE



CASE STYLE: DL1721

CMA-63+

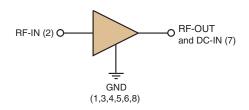
+RoHS Compliant

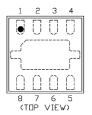
The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

General Description

CMA-63+ (RoHS compliant) is an advanced wideband amplifier fabricated using HBT technology and offers ultra flat gain over a broad frequency range and with high IP3. In addition, the CMA-63+ has good input and output return loss over a broad frequency range without the need for external matching components. Terminal finish is Ni-pd-Au and it has repeatable performance from lot to lot due to fully automated, tightly controlled semiconductor and assembly processes.

simplified schematic and pin description





Function	Pin Number	Description	
RF IN	2	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.	
RF-OUT and DC-IN	7	RF output and bias pin. DC voltage is present on this pin; therefore a DC blocking capacitor is necessary for proper operation. An RF choke is needed to feed DC bias without loss of RF signal due to the bias connection, as shown in "Recommended Application Circuit", Fig. 2	
GND	GND 1,3,4,5,6,8, Bottom Center Paddle Connections to ground. Use via holes as shown in "Suggested Layout for PC to reduce ground path inductance for best performance.		

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Electrical Specifications^{1,2} at 25°C, unless noted

Parameter	Condition (GHz)	Min.	Тур.	Max.	Units
Frequency Range ²		0.01		6	GHz
Gain	0.05		21.9		dB
	0.8	19.0	21.2		
	2.0		20.3		
	3.0		19.0		
	4.0		17.5		
	6.0		14.4		
Gain Flatness	0.05 - 3.0		±1.5		dB
	0.7 - 2.6		±1.2		
Input Return Loss	0.05		16.6		dB
	0.8		20.2		
	2.0		30.0		
	3.0		16.2		
	4.0		11.5		
	6.0		8.9		
Output Return Loss	0.05		15.9		dB
	0.8		19.8		
	2.0		14.9		
	3.0		15.8		
	4.0		16.2		
Reverse Isolation	6.0 2.0		18.5 23.7		dB
	0.05		18.7		dBm
Output Power @1 dB compression	0.05		18.9		ubili
	2.0		18.4		
	3.0		16.3		
	4.0		14.3		
	6.0		11.7		
Output IP3	0.05		34.6		dB
Output II 3	1.0		34.4		
	2.0		32.0		
	3.0		29.2		
	4.0		27.5		
	6.0		25.3		
Noise Figure	0.05		3.7		dB
	1.0		3.9		
	2.0		3.9		
	3.0		3.9		
	4.0		4.1		
	6.0		4.6		
Device Operating Voltage		4.8	5.0	5.2	V
Device Operating Current		58	69	78	mA
Device Current Variation vs. Temperature ³			62		μΑ/°C
Device Current Variation vs. Voltage			0.035		mA/mV
Thermal Resistance, junction-to-ground lead			64		°C/W

⁽¹⁾ Measured on Mini-Circuits Characterization test board TB-656-63+. See Characterization Test Circuit (Fig. 1)

Absolute Maximum Ratings

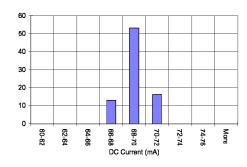
Parameter	Ratings		
Operating Temperature (ground lead)	-55°C to 85°C		
Storage Temperature	-65°C to 125°C		
Operating Current at 5V	120 mA		
Power Dissipation	0.5 W		
Input Power (CW)	13 dBm		
DC Voltage on Pin 3	6V		



Permanent damage may occur if any of these limits are exceeded.

Electrical maximum ratings are not intended for continuous normal operation.

For continuous operation, do not exceed 5.2V device voltage.



Low Frequency cut-off determined by external coupling capacitors and external bias choke
 (Current at 85°C — Current at -45°C)/130

Notes

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Characterization Test Circuit

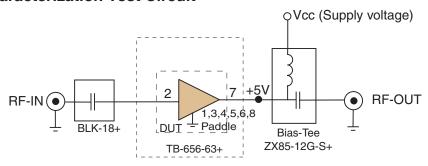


Fig 1. Block Diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Characterization test board TB-656-63+) Gain, Return loss, Output power at 1dB compression (P1 dB), output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

- 1. Gain and Return loss: Pin= -25dBm
- 2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, 0 dBm/tone at output.

Recommended Application Circuit

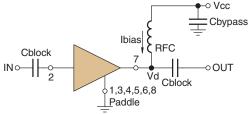
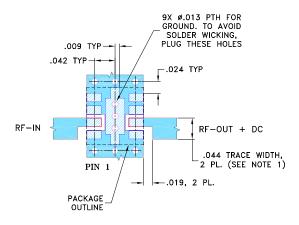


Fig 2. Test Board includes case, connectors, and components soldered to PCB for component values, please see evaluation board drawing.

Suggested PCB Layout (PL-366)



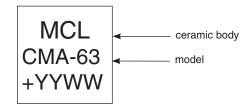
NOTES:

- THICKNESS .020" ± .0015"; COPPER: 1/2 OZ. EACH SIDE. FOR OTHER MATERIALS TRACE WIDTH AND GAP MAY NEED TO BE MODIFIED.

 2. BOTTOM SIDE OF THE PCB IS CONTINUOUS GROUND PLANE.

DENOTES PCB COPPER LAYOUT WITH SMOBC (SOLDER MASK OVER BARE COPPER) DENOTES COPPER LAND PATTERN FREE OF SOLDER MASK

Product Marking



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